EAST Search History

EAST Search History (Prior Art)

Ref#	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L24	8	"596126".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 22:02
L19	45	(luminous or light near emitti\$3 or active or single quantum well or SCW)same(grad\$3 or var\$3) same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((56 m² "b" or "0.5" or "0.6" or "0.7" or "0.8") and (InGaN or "In.sub.x Ga.sub.1-x N or "In.sub.x Ga.sub.1-x N or "In.sub.x Ga.sub.1-x N or "In.sub.x Ga.sub.1" Ga.sub." "Ga.sub." "Ga.sub." "Ga.sub." "Ga.sub." "Ga.sub." "Ga.sub." "Ga.sub." "AlGaIn N or GaN or AlGaIn M or GaN or AlGaIn M or GaN or AlGaIn M or GaN o	US-POPUB: USPAT: USPOR: PPRS: EPO: JPO; DETWENT: IBM_TDB	ADJ	ON .	2010/11/05 21:48
L18	34	(active or single quantum well or SOW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$5 or mol or mole or content) same ((56 (*) ***) or "0.5" or "0.5" or "0.5" or "0.7" or "0.8") and (InGaN or "In.sub.x Ga.sub.1-x N Y or "In.sub.x Ga.sub.1-x N Y or "In.sub.x Ga.sub.1-x N Y or "In.sub.1+x N Y or "In.sub.1+x N Y or "In.sub.1+x N Y Or "A Gall N Or Gall Or AlGaln N or Gall Or AlGaln Or Gall Or AlGaln Or Gall Or Vall Or Vall Or Gall Or AlGaln Or Gall Or Vall Or Vall Or Vall Or Vall Or Vall Or Gall Or Vall Or	US-PATUR: USPAT: USOCR FPRS: EPO: JPO: DEFWENT: IBM_TDB	ADJ	ON	2010/11/05 21:42

L17	138	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or	US-PGPUB; USPAT; USOCR; FPRS, EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 21:41
		(Indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5[d] "%" or "80" %") or (".5[d]" or "1")) and (InGaN or "In.sub.x Ga.sub.1 x N" or "In.sub.x Ga.sub.1 -a, ub.1 -1, apha.N") and ("Al.sub.x" "Ga.sub," "In.sub.1 +x-y" N or AlGaInN or GaN or AlGaInN or GaN or AlGaInN or GaN or AlGaInN or GaN or Concentration or content or conte				
L16	***************************************	(active or single quantum well or SOW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5 d)"%" or (".5 d)")) and (InGaN or "In.sub. x Ga.sub.1-x.alpha. R)" and ("Alsub. x" "Ga.sub.3" in. sub.1-x-y" N or AlGaInN or GaN or AlGaN)	US-AGPUB; US-PAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	07	2010/11/05 21:39
L15	65	(active or single quantum well or SOW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d})"%" or "80"%"") and ((1GAN or "In sub. alpha Ga. sub. 1-x N' or "In sub. alpha Ga. sub. 1-alpha N') and ("Al sub. x" "Ga. sub, "In sub. 1-x-y" N or AlGalnN or GaN or	US-PGPUB; USPAT; USCOR; FPRS; EPC; JPC; DERWENT; IBM_TDB	ADJ	ON .	2010/11/05 21:38

L14	107	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((\$G\) or "80""s\"1" and (InGaN or "In.sub. x Ga.sub.1-x N' or "In.sub.x Ga.sub.1-x N' or "In.sub.x Ga.sub.1" ("Al.sub.x" "Ga.sub.y" "In.sub.x" "Ga.sub.y" "In.sub.x" "AlGaln N or GaN or AlGaln or GaN or AlGaln or AlGaln or AlGaln or Algaln or Vallagan or Vallaga	US PAPUB. USPAT. USOCR, FPRS. EPO. JPO. DERWENT: IBM_TDB	ADJ	ON	2010/11/05 21:36
	107	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or vars\$3)same ((Indium or In) near2 (high or rich) or (indium or In) same (concentration or composition\$2 or mol or mole or content) same ((5[d] or "80""6") or (5[d] or "18.9") and (InGaN or "1n.sub.x Ga.sub.1-x N" or "In.sub.x Ga.sub.1-x N" or "In.sub.x Japha.Ra.sub.1-alpha.N") and ("Als.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGaIn N or GaN or AlGaN or AlGaN)	US PGPUB; USPAT; USOCR; PFRS; EPO; JPO; DEBWENT; IBM_TDB	ADJ	ON	2010/11/05 21:34
L12	103	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In) same (concentration or composition\$2 or mol or mole or content) same ((5{d}) or "80")"%" or (5{d}) or "180") and (InGaN or "In sub. x Ga sub.1-x N" or "In sub. x Ga sub.1-x N" or "In sub. alpha Ga sub.1-alpha N") and ("Al sub.x" "Ga sub," "In sub.1-x-y" N or AlGaInN or GaN or A	US PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 21:33

L11	***************************************	(active or single quantum well or SOW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5/6) or ".8")) and (InGaN or "In.sub.x Ga. sub.1-x Nr or "In.sub. alpha. Ga. sub.1-x In, sub.1-x Nr or A'GainN or GaN or A'GanN or A'GainN or GaN or A'GainN or GaN or A'GainN or GaN or A'GanN or A'GainN or GaN or A'GainN or A'GainN or GaN or A'GainN or A'GainN or A'GainN or GaN or A'GainN or Gan or A'GainN or Gan or A'GainN or Gan or A'GainN o	US-PATUR: USPAT: USOCR: FPRS: EPO; JPO; DEFWENT: IBM_TDB	ADJ	ON	2010/11/05 21:32
L10	73	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In) same (concentration or composition\$2 or mol or mole or content) same ((5{q}) or "80") or "(".5" (14:2))) and (InGaN or "In.sub.x Ga. sub.1-x N" or "In.sub., alpha. Ca. sub.1-x "In. sub. 1-x-y" N or AlGaInN or GaN or AlGaInN or GaM or AlGAIN o	US POPUB: USPAT: USPOR: FPRS: EPO: JPO; DEFWENT: IBM_TDB	ADJ	ON	2010/11/05 21:20
L9	402	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) and (InGaN or "In.sub. apha. Ga.sub.1 ajpha.N" and ("Al.sub. x" "Ga.sub.1 ajpha.N" and "Al.sub. x" "Ga.sub.y" "In.sub. 1 xy" N or AlGalnN or GaN or AlGaN)	US PGPUB; USPAT; USPOR; PFPS; EPO; JPO; DEFWENT; IBM_TDB	ADJ	ON	2010/11/05 20:57

L6	257	(active or single quantum well or SQW) same gradS3 and ((Indium or In) near2 (high or rich) or (indium or In) same (composition\$2 or mole or content) and (InGaN or "In sub. x Ga sub.1-x N") and ("Al sub x" "Ga. sub y" "In sub. 1-x-y" N or AlGaln N or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO, JPO, DERWENT; IBM_TDB	ADJ	ON	2010/11/05 20:14
L5	255	(active or single quantum well or SOW) same grad\$3 and (((Indium or In) near2 (high or rich) or (indium or In)) same (composition or mol or mole or content) and (InGaN or "In sub. x Ga. sub.1-x N") and ("Al. sub.x" "Ga. sub," "In sub.1-x," N or A/GaIn N or GaN or A/GaN)	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AOJ	ON .	2010/11/05 20:06
L4	40	(active or single quantum well or SOW) same grad\$3 and ((Indium or In) near2 (high or rich) or (indium or In)) same (composition or mol or mole or content) and (InGaN or "In.sub.x Ga. sub.1-x N") and ("Al. sub.x" "Ga. sub.y" "In. sub.1-x-y" N or AlGaInN) and GaN	US-PGPUB; USPAT; USOOR; FPRS, EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 20:04
L3	40	(active or single quantum well or SQW) same grad\$3 and (((Indium or In) near2 (high or rich) or (indium or In)) same (composition or mol or content) and ((InGaN or "In sub. x Ga. sub.1+x N") and "Nl. sub.x" "Ga. sub.y" "In. sub.1+x"," N or AlGaInN)	US-PGPUB; USPAT; USOOR; FPRS; EPO, JPO; DERWENT; IBM_TDB	ADJ	ON .	2010/11/05 20:03

L2	10	[(active or single quantum well or SOW) same grad\$3 and ((Indium or In) near2 (high or rich) and ((InGaN or "In.sub.x Ga. sub.1-x N") and ("Al. sub x" "Ga.sub.y" "In. sub.1-x-y" N or A(GaI nN)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	NO.	2010/11/05 19:59
L1		(active or single quantum well or SOW) same (Indium or In) near2(high or rich) same grad\$3 and (InGaN or "In.sub.x Ga. sub.1-x N") and ("Al. sub.x" "Ga. sub.y" "In. sub.1-x-y" N or A(GaI nN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 19:56
S190	1041	257/e33.008.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 16:56
S189	212	graded same (single quantum well or SQW or active) same indium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 16:37
S188	8	graded same single quantum well same indium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 15:20
S187	20	growth near interruption same indium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 15:10
S186	31	257/e33.03.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 12:20
S185	8	257/e33.031.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 12:19
S184	28	257/e33.026.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 12:15

S183	228	257/e33.025.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 12:11
S182	280	257/e33.023.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:56
S181	20	257/e33.016.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:55
S180	400	257/85.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:44
S179	520	257/9.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:38
S178	140	257/28.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:34
S177	535	257/e29.298.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:25
S176	95	single quantum well same graded same (indium or (In))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 10:56
S175	94	single quantum well same graded same (indium or (In))	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/11/05 10:55
S174	114	("5247533" "5290393" "5290393" "5290393" "530662" "5334277" "5433169" "5468678" "5583879" "5604763" "562502").PN. OR ("5834331").URFN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/05 10:10

S173	17	(ultra\$violet or UV) near light near emitt\$3 and (high or rich)near (indium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 10:00
S172	217	(ultra\$violet or UV) near light near emitt\$3 and (high or rich)near (indium or In)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 10:00
S171	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.64"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:59
S170	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.63"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S169	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.62"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S168	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.65"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S167	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.9"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S166	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.8"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S165	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.7"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S164	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.58"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S163	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.52"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58

S162	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.51"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S161	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.55"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S160	12	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.5"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:56
S159	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.6"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:56
S158	10250	(ultra\$violet or UV) near light near emitt\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:56
S157	172	257/e29.033.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:53
S156	106	257/e29.072.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:46
S155	215	257/e29.07.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:46
S154	99	257/e29.069.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:40
S153	36	grading with (indium) same (quantum near well or active or QW)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 00:02
S152	1	grading with (indium) and ultraviolet and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 00:01

S151	70	grading with (indium or In)and ultraviolet and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 00:01
S150	4	grading near (indium or In)and ultraviolet and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 00:00
S149	300	grading near (indium or In)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/04 23:59
S148	8	"596126".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/04 23:06
S147	43	("5617446" "5670798").PN. OR ("5889295").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/04 22:34
S146	147	inGaN and (ultraviolet or UV or ultra-violet) and (indium)same (quantum near well or active) and 257/11-15. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 21:59
S145	333	inGaN and (ultraviolet or UV or ultra-violet) and (indium or In) same (quantum near well or active) and 257/11-15.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 21:50
S144	126	InGaN and (ultraviolet or UV or ultra-violet) and (indium or In) same (quantum near well or active) and 257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 21:50
S143	135	InGaN and (ultraviolet or UV or ultra-violet) and 257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:43
S142	110	InGaN and ultraviolet and 257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:43

S141	251	InGaN and 257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:42
S140	1308	257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:41
S139	7	emitt\$3 same (ultraviolet or ultra- violet or UV) and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:35
S138	0	In near Ga near N and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:25
S137	1	In-rich and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:25
S136	1	In near GaN and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:24
S135	3	InGaN and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:24
S134	403	seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:24
S133	1	((PILKYUNG) near2 (MOON)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/04 18:23
S132	1	((SOON-YONG) near2 (KWON)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/04 18:21
S131	3	((EUIJOON) near2 (YOON)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/04 18:18
S130	1	(ultraviolet or UV)emitt \$3 (indium near rich or In near rich) quantum near well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2010/11/04 18:18

S129	0	(ultraviolet or UV)emitt \$3 (indium near rich or In near reach) quantum near well		SAME	ON	2010/11/04 18:18
S128	11	(ultraviolet or UV)emitt \$3 (InGaN or In near Ga near N)near quantum near well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/11/04 18:03
S127	471	(ultraviolet or UV)emitt \$3 (InGaN or In near Ga near N)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/11/04 18:02

EAST Search History (Interference)

Ref#	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L23	47	((luminous or light near emitt\$3 or active or single quantum well or SCM) and(grad\$3 or vay\$3) same ((Indium or In) near2(high or rich) or (indium or In) near2(high or rich) or (indium or In) same (concentration or composition\$2 or mol or mole or content)same ((5 [d] "%" or "80""%") or ("0.5" or "0.7" or "0.8") and (InGaN or "In.sub. Xa.sub.1-x N" or "In. sub. xipha. Ga.sub.1-x lapha. N") and ('InSub. "Ga.sub.1-x lapha. N") and ('InSub. "Ga.sub.1-x lapha. N") and ('InSub. "Ga.sub.1-x lapha. N") and ('InSub. "190. Sub. 1-x y") N or A(GaInN or GaN) and S7/(-15.E. 29.09.09.E. 29.07.E. 29.07.2. E29.033.E33.016.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.03.E33.E3	US- PGPUB; USPAT; UPAD	ADJ	ON	2010/11/05 21:55
L22	2		US- PGPUB; USPAT; UPAD	ADJ	ON	2010/11/05 21:51

L21	0	[((Iuminous or light near emitt\$3 or active or single quantum well or SCM)same(grad\$3 or vary\$3 or var \$3)same ((Indium or In) near2(high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content)same ((5 (d) %° or "60"%") or ("0.5" or "0.6" or "0.7" or "0.8") and (InGaN or "In.sub.x Ga.sub.1-x N" or "In.sub.x Ga.sub.y" in.sub.x 1-x y" N or AlGalnN or GaN or AlGaN)). clm.	US- PGPUB; USPAT; UPAD	ADJ	ON	2010/11/05 21:50
L20	45	(luminous or light near emitt\$3 or active or single quantum well or SSUM)same(qrad\$3 or vary\$3)same ((Indium or In) near2(high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content)same (5 (d) "%" or "80" "%") or "("0.5" or "0.7" or "0.8") and (InGaN or "In.sub. alpha.Ga.sub.1-x N" or "In. sub. alpha.Ga.sub.1-x y" N or AGalnN or GaN or AGaN)	US- PGPUB; USPAT; UPAD	ADJ	ON	2010/11/05 21:50

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